16-bit Buffer / Driver with 3-state Outputs

HITACHI

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Description

The HD74ALVC162244 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical $\overline{\text{OE}}$ (active-low output-enable) inputs.

To ensure the high impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

All outputs, which are designed to sink up to 12 mA, include equivalent 26 Ω resistors to reduce overshoot and undreshoot.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current $\pm 12 \text{ mA}$ (@V_{CC} = 3.0 V)
- All outputs have equivalent 26 Ω series resistors, so no external resistors are required



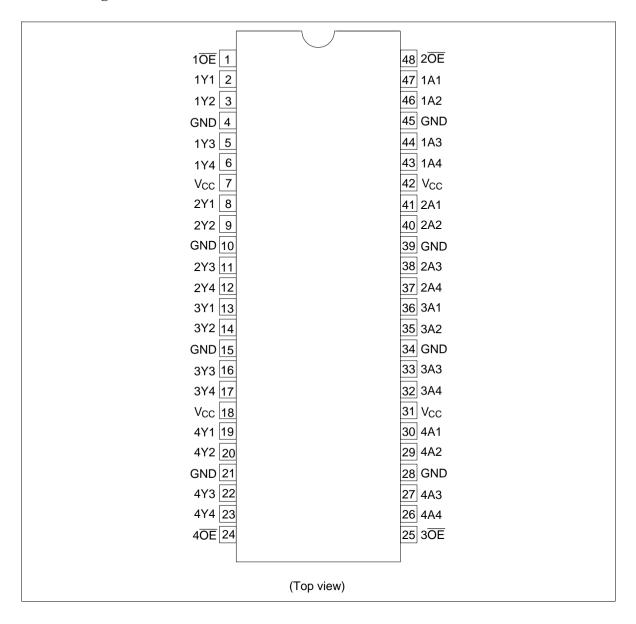
Function Table

Inputs		Output Y			
ŌE	A				
L	Н	Н			
L	L	L			
Н	X	Z			

H: High level
L: Low level
X: Immaterial

Z : High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 4.6	V	
Input voltage *1	V _I	-0.5 to 4.6	V	
Output voltage *1,2	Vo	-0.5 to V_{cc} +0.5	V	
Input clamp current	I _{IK}	– 50	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_o < 0 \text{ or } V_o > V_{cc}$
Continuous output current	Io	±50	mA	$V_{\rm o}$ = 0 to $V_{\rm cc}$
V _{cc} , GND current / pin	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) ^{'3}	P _T	0.85	W	TSSOP
Storage temperature	T_{stg}	-65 to 150	°C	

Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

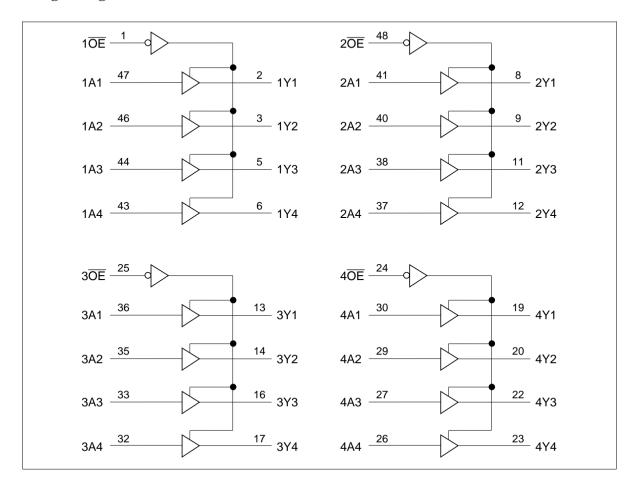
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{cc}	2.3	3.6	V	
Input voltage	V_{I}	0	V_{cc}	V	
Output voltage	Vo	0	V _{cc}	V	
High level output current	I _{OH}	_	-6	mA	V _{CC} = 2.3 V
		_	-8		$V_{CC} = 2.7 \text{ V}$
		_	-12		$V_{CC} = 3.0 \text{ V}$
Low level output current	I _{OL}	_	6	mA	V _{CC} = 2.3 V
		_	8		$V_{CC} = 2.7 \text{ V}$
		_	12		$V_{CC} = 3.0 \text{ V}$
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	T _a	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



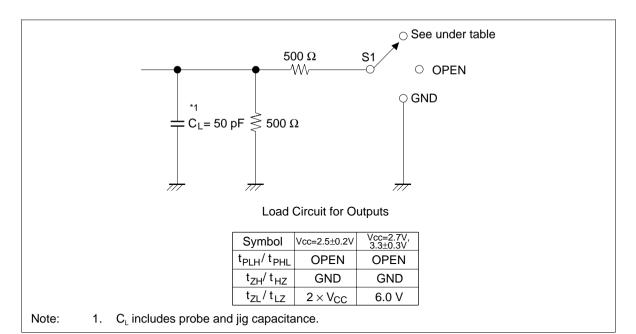
Electrical Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Item	Symbol	V _{cc} (V)	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	_	
	V _{IL}	2.3 to 2.7	_	0.7	_	
		2.7 to 3.6	_	0.8	-	
Output voltage	V_{OH}	2.3 to 3.6	V _{cc} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	1.9	_	-	$I_{OH} = -4 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_		$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		3.0	2.4	_		$I_{OH} = -6 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		2.7	2.0	_	-	$I_{OH} = -8 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{OL}	2.3 to 3.6	_	0.2		I _{OL} = 100 μA
		2.3	_	0.4	_	$I_{OL} = 4 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.55	-	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		3.0	_	0.55	-	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		2.7	_	0.6	_	$I_{OL} = 8 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.8	-	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I _{IN}	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
Off state output current	I _{oz}	3.6	_	±10	μΑ	$V_{OUT} = V_{CC}$ or GND
Quiescent supply current	I _{cc}	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	750	μА	V_{IN} = one input at (V_{CC} -0.6) V, other inputs at V_{CC} or GND

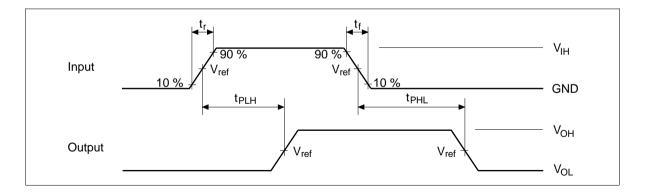
Switching Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH}	2.5±0.2	1.0	_	4.9	ns	А	Υ
	$t_{\tiny PHL}$	2.7	_	_	4.7			
		3.3±0.3	1.0	_	4.2			
Output enable time	t _{zH}	2.5±0.2	1.0	_	6.8	ns	ŌĒ	Υ
	t_{zL}	2.7	_	_	6.7			
		3.3±0.3	1.0	_	5.6			
Output disable time	t _{HZ}	2.5±0.2	1.0	_	6.3	ns	ŌĒ	Υ
	\mathbf{t}_{LZ}	2.7	_	_	5.7			
		3.3±0.3	1.0	_	5.5			
Input capacitance	C _{IN}	3.3	_	3.0	_	pF	Control in	outs
		3.3	_	6.0	_		Data input	S
Output capacitance	C _o	3.3	_	7.0	_	pF	Outputs	

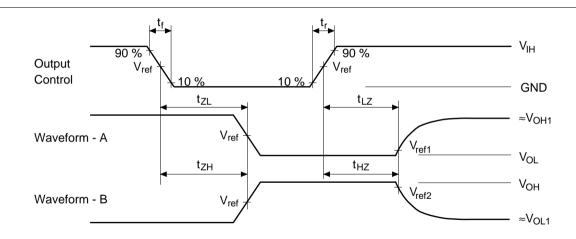
Test Circuit



Waveforms - 1



Waveforms – 2



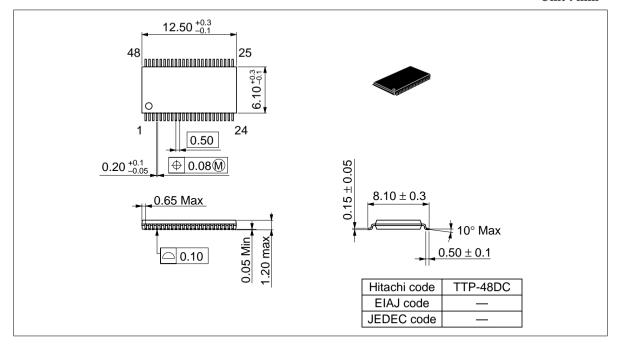
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V _{IH}	V_{CC}	2.7 V
V _{ref}	1/2 V _{CC}	1.5 V
V _{ref1}	V _{OL} +0.15 V	V _{OL} +0.3 V
V _{ref2}	V _{OH} -0.15 V	V _{OH} -0.3 V
V _{OH1}	V_{CC}	3.0 V
V _{OL1}	GND	GND

Notes:

- 1. All input pulses are supplied by generators having the following characteristics : PRR \leq 10 MHz, Zo = 50 Ω , $t_r \leq$ 2.0 ns, $t_f \leq$ 2.0 ns. (V_{CC} = 2.5 \pm 0.2 V) PRR \leq 10 MHz, Zo = 50 Ω , $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns. (V_{CC} = 2.7 V, 3.3 \pm 0.3 V)
- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit: mm



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